



## Triacs sensitive gate

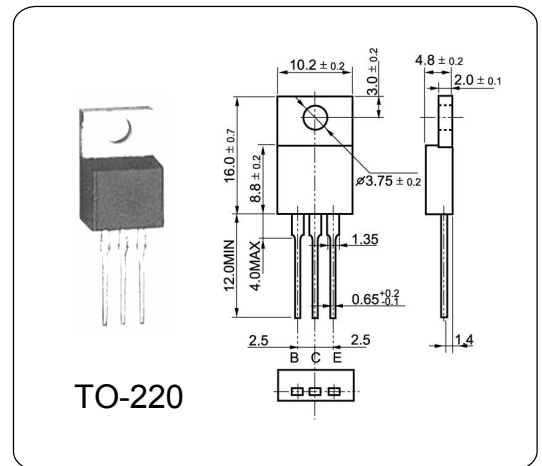
## 5P4M 5P5M 5P6M

### GENERAL DESCRIPTION

Passivated thyristors in a plastic envelope, intended for use in applications requiring high bidirectional blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial domestic lighting, heating and static and switching.

### ABSOLUTE MAXIMUM RATINGS ( Ta = 25 °C)

Parameter	Symbol	Typ			Unit
		5P4M	5P5M	5P6M	
Repetitive peak off-state voltages	$V_{DRM}$ $V_{RRM}$	400	500	600	V
RMS on-state current	$I_{T(AV)}$	5.0			A
Non-repetitive peak on-state current	$I_{TSM}$	80			A
Max. Operating Junction Temperature	$T_j$	110			°C
Storage Temperature	$T_{stg}$	-45~150			°C



### ELECTRICAL CHARACTERISTICS ( Ta = 25 °C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Repetitive peak off-state voltages	$V_{DRM}$ $V_{RRM}$		—	400 ~600	—	V
RMS on-state current	$I_{T(AV)}$	full sine wave; $T_{mb} \leq 103\text{ °C}$	—	5.0	—	A
On-state voltage	$V_T$	$I_T = 10A$	—	—	1.4	V
Holding current	$I_H$	$V_D = 24\text{ V}; I_{GT} = 0.1\text{ A}$	—	10	—	mA
Gate trigger current	$I_{GT}$	$V_D = 6.0\text{ V}; R_L = 100\ \Omega$	—	—	10	mA
Gate trigger voltage	$V_{GT}$	$V_D = 6.0\text{ V}; R_L = 100\ \Omega$	—	—	1.5	V